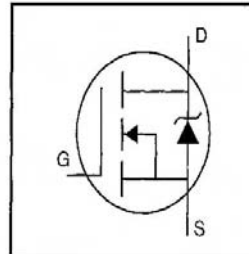


# IRFIBE30GPbF

HEXFET® Power MOSFET

- Isolated Package
- High Voltage Isolation= 2.5KVRMS ⑤
- Sink to Lead Creepage Dist.= 4.8mm
- Dynamic dv/dt Rating
- Low Thermal Resistance
- Lead-Free

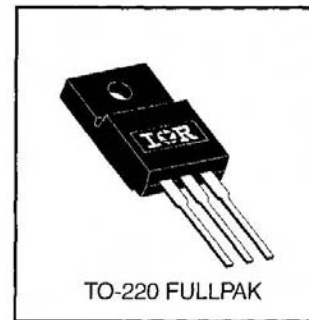


$V_{DSS} = 800V$   
 $R_{DS(on)} = 3.0\Omega$   
 $I_D = 2.1A$

### Description

Third Generation HEXFETs from International Rectifier provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220 Fullpak eliminates the need for additional insulating hardware in commercial-industrial applications. The moulding compound used provides a high isolation capability and a low thermal resistance between the tab and external heatsink. This isolation is equivalent to using a 100 micron mica barrier with standard TO-220 product. The Fullpak is mounted to a heatsink using a single clip or by a single screw fixing.



### Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10 V$	2.1	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10 V$	1.4	
$I_{DM}$	Pulsed Drain Current ①	8.4	
$P_D @ T_C = 25^\circ C$	Power Dissipation	35	W
	Linear Derating Factor	0.28	W/°C
$V_{GS}$	Gate-to-Source Voltage	±20	V
$E_{AS}$	Single Pulse Avalanche Energy ②	240	mJ
$I_{AR}$	Avalanche Current ①	2.1	A
$E_{AR}$	Repetitive Avalanche Energy ①	3.5	mJ
dv/dt	Peak Diode Recovery dv/dt ③	2.0	V/ns
$T_J$ $T_{STG}$	Operating Junction and Storage Temperature Range	-55 to +150	°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting Torque, 6-32 or M3 screw	10 lbf•in (1.1 N•m)	

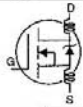
### Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	3.6	°C/W
$R_{\theta JA}$	Junction-to-Ambient	—	—	65	

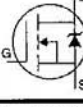
# IRFIB30GPbF

International  
IR Rectifier

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

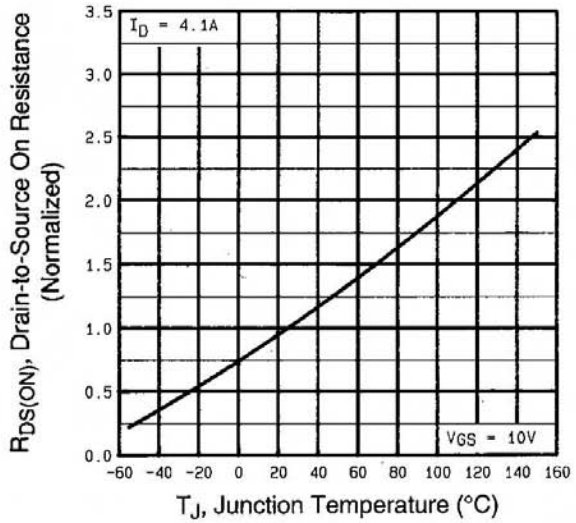
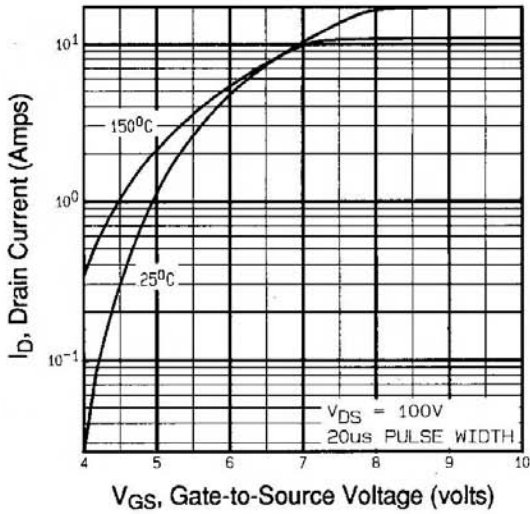
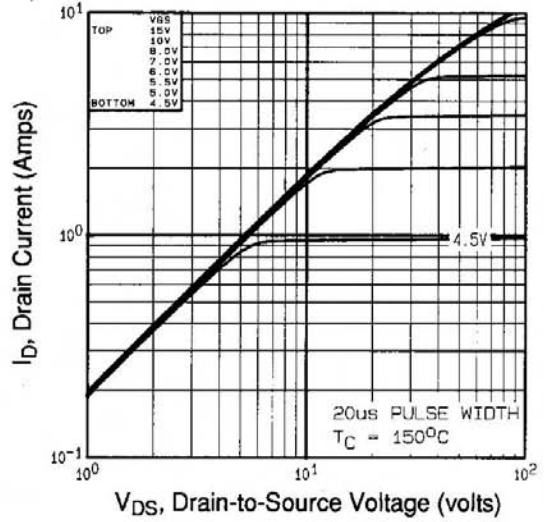
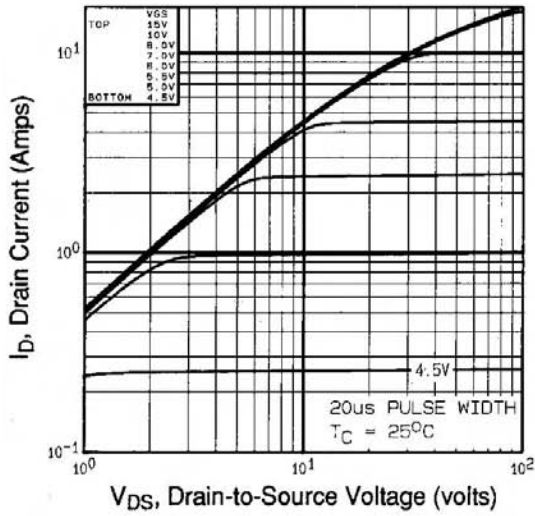
	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	800	—	—	V	$V_{GS}=0V, I_D=250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.90	—	V/°C	Reference to $25^\circ\text{C}$ , $I_D=1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	3.0	$\Omega$	$V_{GS}=10V, I_D=1.3A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS}=V_{GS}, I_D=250\mu A$
$g_{fs}$	Forward Transconductance	1.7	—	—	S	$V_{DS}=50V, I_D=1.3A$ ④
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	100	$\mu A$	$V_{DS}=800V, V_{GS}=0V$
		—	—	500		$V_{DS}=640V, V_{GS}=0V, T_J=125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS}=20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS}=-20V$
$Q_g$	Total Gate Charge	—	—	78	nC	$I_D=4.1A$
$Q_{gs}$	Gate-to-Source Charge	—	—	9.6		$V_{DS}=400V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	—	45		$V_{GS}=10V$ See Fig. 6 and 13 ④
$t_{d(on)}$	Turn-On Delay Time	—	12	—	ns	$V_{DD}=400V$
$t_r$	Rise Time	—	33	—		$I_D=4.1A$
$t_{d(off)}$	Turn-Off Delay Time	—	82	—		$R_G=12\Omega$
$t_f$	Fall Time	—	30	—		$R_D=95\Omega$ See Figure 10 ④
$L_D$	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6 mm (0.25in.) from package and center of die contact 
$L_S$	Internal Source Inductance	—	7.5	—		
$C_{iss}$	Input Capacitance	—	1300	—	pF	$V_{GS}=0V$
$C_{oss}$	Output Capacitance	—	310	—		$V_{DS}=25V$
$C_{rss}$	Reverse Transfer Capacitance	—	190	—		$f=1.0\text{MHz}$ See Figure 5
C	Drain to Sink Capacitance	—	12	—		$f=1.0\text{MHz}$

## Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	2.1	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	8.4		
$V_{SD}$	Diode Forward Voltage	—	—	1.8	V	$T_J=25^\circ\text{C}, I_S=2.1A, V_{GS}=0V$ ④
$t_{rr}$	Reverse Recovery Time	—	480	720	ns	$T_J=25^\circ\text{C}, I_F=4.1A$
$Q_{rr}$	Reverse Recovery Charge	—	1.8	2.7	$\mu C$	$di/dt=100A/\mu s$ ④
$t_{on}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S+L_D$ )				

### Notes:

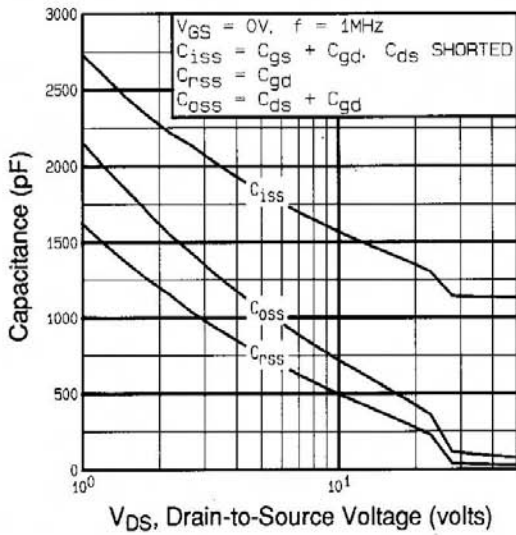
- ① Repetitive rating; pulse width limited by max. junction temperature (See Figure 11)
- ②  $V_{DD}=50V$ , starting  $T_J=25^\circ\text{C}$ ,  $L=102\text{mH}$ ,  $R_G=25\Omega$ ,  $I_{AS}=2.1A$  (See Figure 12)
- ③  $I_{SD}\leq 4.1A$ ,  $di/dt\leq 100A/\mu s$ ,  $V_{DD}\leq 600$ ,  $T_J\leq 150^\circ\text{C}$
- ④ Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$
- ⑤  $t=60s$ ,  $f=60\text{Hz}$



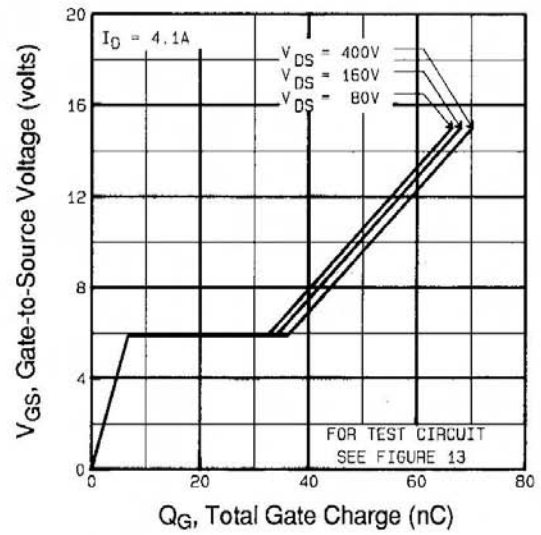


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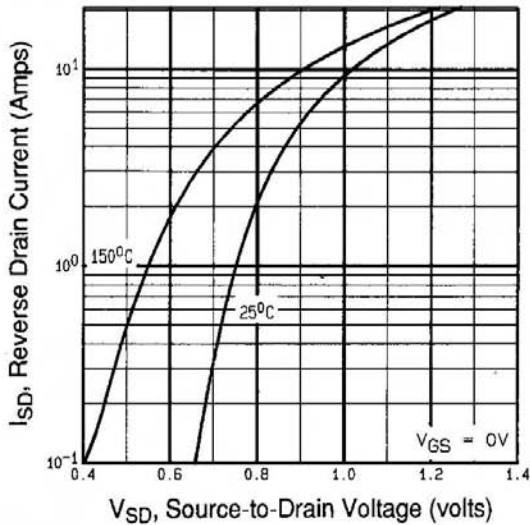
International  
**IR** Rectifier



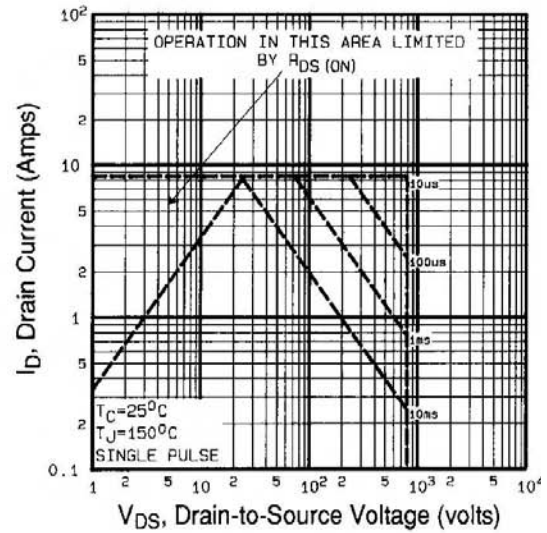
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



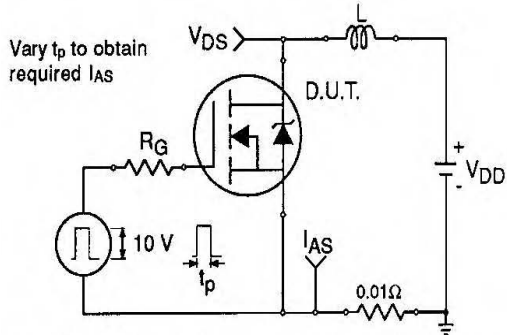
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



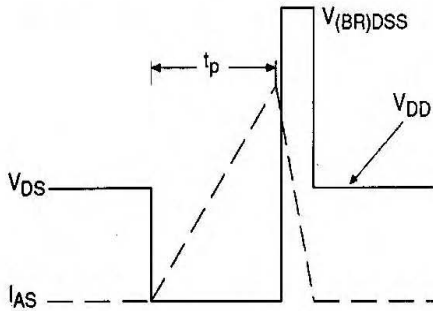
**Fig 7.** Typical Source-Drain Diode Forward Voltage



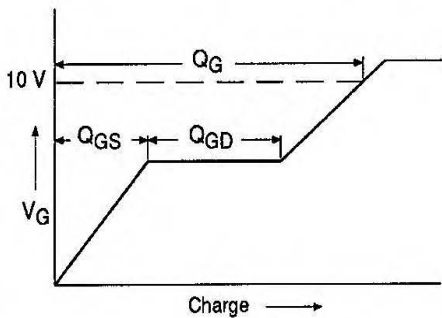
**Fig 8.** Maximum Safe Operating Area



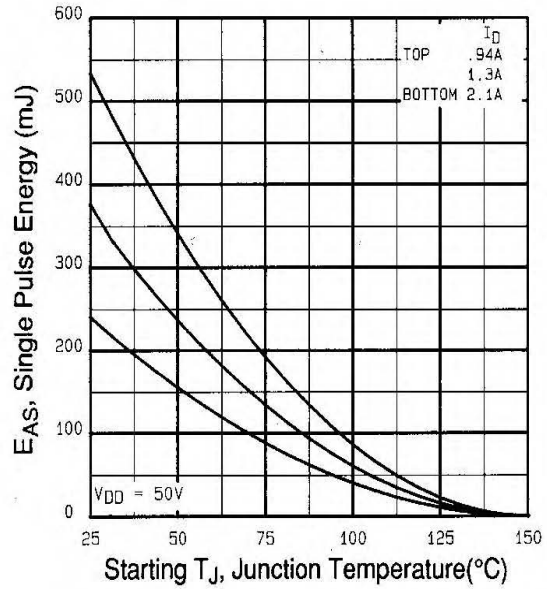
**Fig 12a.** Unclamped Inductive Test Circuit



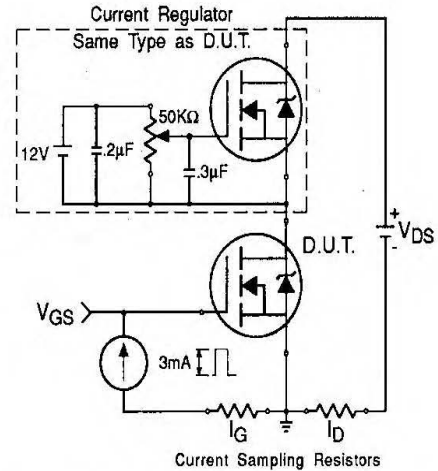
**Fig 12b.** Unclamped Inductive Waveforms



**Fig 13a.** Basic Gate Charge Waveform

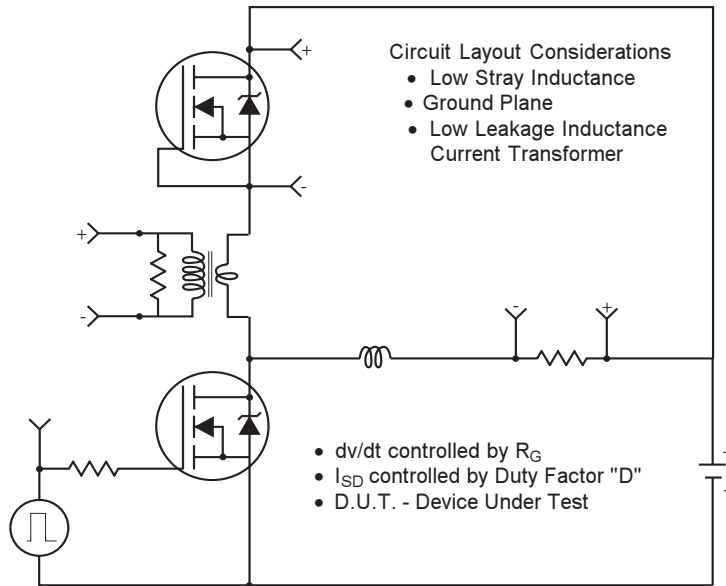


**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current



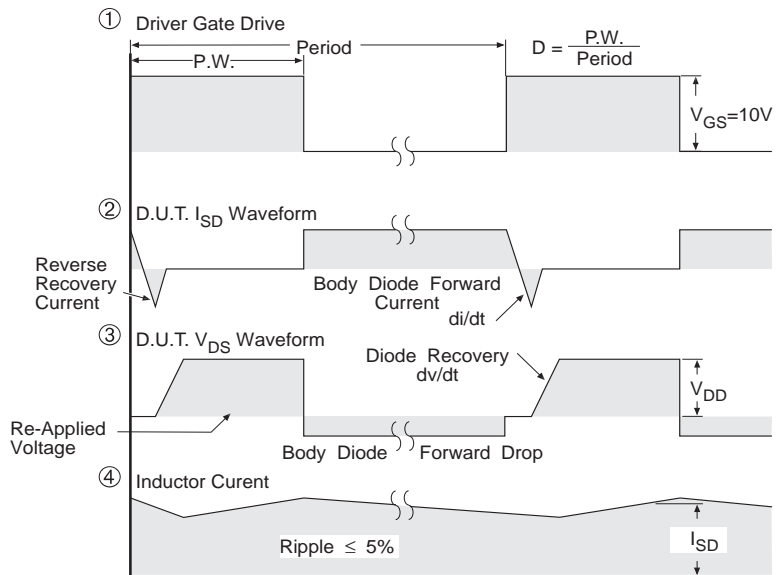
**Fig 13b.** Gate Charge Test Circuit

## Peak Diode Recovery dv/dt Test Circuit



\* Reverse Polarity for P-Channel

\*\* Use P-Channel Driver for P-Channel Measurements

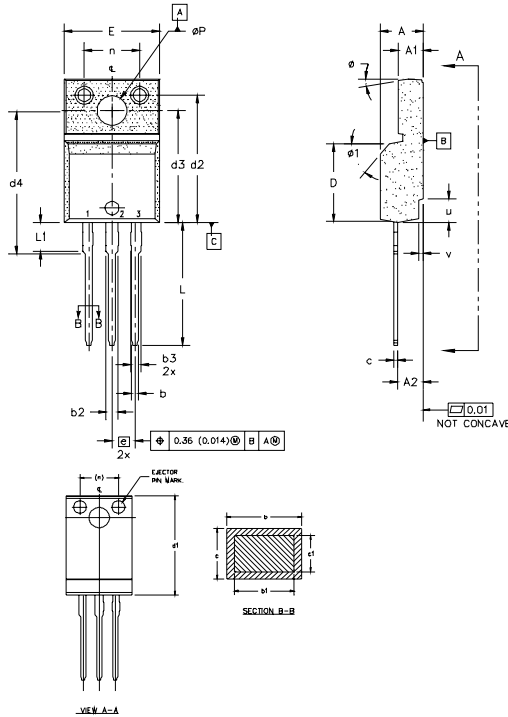


\*\*\*  $V_{GS} = 5.0V$  for Logic Level and 3V Drive Devices

**Fig -14** For N Channel HEXFETS

## TO-220 Full-Pak Package Outline

Dimensions are shown in millimeters (inches)



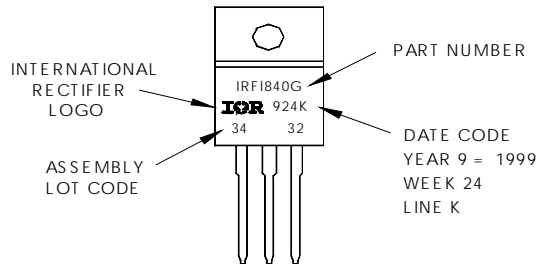
- NOTES:
- 1.0 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
  - 2.0 DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
  - 3.0 LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
  - 4.0 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
  - 5.0 DIMENSION b1 APPLY TO BASE METAL ONLY.
  - 6.0 STEP OPTIONAL ON PLASTIC BODY DEFINED BY DIMENSIONS u & v.
  - 7.0 CONTROLLING DIMENSION : INCHES.

SYMBOL	DIMENSIONS				NOTES	LEAD ASSIGNMENTS
	MILLIMETERS		INCHES			
	MIN.	MAX.	MIN.	MAX.		
A	4.57	4.83	0.180	0.190		
A1	2.57	2.83	0.101	0.114		
A2	2.51	2.85	0.099	0.112		
b	0.622	0.89	0.024	0.035		HEXFET 1.- GATE 2.- DRAIN 3.- SOURCE
b1	0.622	0.858	0.024	0.033	5	
b2	1.229	1.400	0.048	0.055		
b3	1.229	1.400	0.048	0.055		
c	0.440	0.629	0.017	0.025		
c1	0.440	0.584	0.017	0.023		IGBTs, CoPACK
D	8.65	9.80	0.341	0.386	4	1.- GATE 2.- COLLECTOR 3.- EMITTER
d1	15.80	16.12	0.622	0.635		
d2	13.97	14.22	0.550	0.560		
d3	12.30	12.92	0.484	0.509		
d4	8.64	9.91	0.340	0.390		
E	10.36	10.63	0.408	0.419	4	
e	2.54 BSC		0.100 BSC			
L	13.20	13.73	0.520	0.541		
L1	3.10	3.50	0.122	0.138	3	
n	6.05	6.15	0.238	0.242		
p	3.05	3.45	0.120	0.136		
u	2.40	2.50	0.094	0.098	6	
v	0.40	0.50	0.016	0.020	6	
ø1	3°	45°	3°	7°		

## TO-220 Full-Pak Part Marking Information

EXAMPLE: THIS IS AN IRF1840G  
 WITH ASSEMBLY  
 LOT CODE 3432  
 ASSEMBLED ON WW 24 1999  
 IN THE ASSEMBLY LINE "K"

**Note:** "P" in assembly line position indicates "Lead-Free"



Data and specifications subject to change without notice.